

Integrated Device Technology, Inc. 6024 Silver Creek Valley Road, San Jose, CA 95138

PRODUCT/	PROCESS CHANGE NOTICE (PCN)				
PCN #: N1408-01 DATE: Product Affected: 874208BKILF 874208BKILFT Date Effective: September 9, 201	September 9, 2014 MEANS OF DISTINGUISHING CHANGED DEVICES: Product Mark Back Mark Date Code Other Shipment after PCN effective date.				
Contact: TSD Clock Team	Attachment: Yes No				
E-mail: <u>clocks@idt.com</u>	Samples: Contact your local sales representative for sample and datasheet requests.				
DESCRIPTION AND PURPOSE OF C □ Die Technology □ Wafer Fabrication Process □ Assembly Process □ Equipment □ Material □ Testing □ Manufacturing Site ■ Data Sheet □ Other - Die revision	The Data Sheet parameter for "Input Resistance" and "Differential Input Resistance" are updated, which allow input specification to be TIA/EIA-644-A compliant. This is an update of the datasheet only, no change of the silicon design, die revision, circuitry, process or device performance.				
RELIABILITY/QUALIFICATION SUR There is no expected change to the produce					
to grant approval or request additional infi it will be assumed that this change is acce	tten notification of this change. Please use the acknowledgement below or E-Mail formation. If IDT does not receive acknowledgement within 30 days of this notice				
Customer:	\Box Approval for shipments prior to effective date.				
Name/Date:	E-Mail Address:				
Title:	Phone # /Fax #:				
CUSTOMER COMMENTS:					
IDT ACKNOWLEDGMENT OF RECI	EIPT:				
RECD. BY:	DATE:				

PRODUCT/PROCESS CHANGE NOTICE (PCN)

ATTACHMENT I - PCN #: N1408-01

PCN Type: Data Sheet Change

Data Sheet Change: Yes

Detail of Change:

From:

Table 4B. LVCMOS/LVTTL Input DC Characteristics, $V_{\rm DD}$ = $V_{\rm DDO}$ = 2.5V, $T_{\rm A}$ = -40°C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V _{IH}	Input High Voltage			1.7		V _{DD} + 0.3	٧
V _{IL}	Input Low Voltage			-0.3		0.7	V
I _{IH}	Input High Current	FSEL1, FSEL0, ADR[1:0]	$V_{DD} = V_{IN} = 2.625V$			150	μΑ
		SCK, SDA	$V_{DD} = V_{IN} = 2.625V$			5	μА
I _{IL}	Input Low Current	FSEL1, FSEL0, ADR[1:0]	$V_{DD} = 2.625V, V_{IN} = 0V$	-5			μΑ
		SCK, SDA	V _{DD} = 2.625V, V _{IN} = 0V	-150			μА
V _{IN}	Input Voltage Swing	IN, nIN		0.15		1.2	٧
V _{CMR}	Common Mode Input Voltage; NOTE 1			1.2		V _{DD}	V
V _{DIFF}	Differential Input Voltage Swing	IN, nIN		0.3		2.4	v
R _{IN}	Input Resistance	IN, nIN to V _T		40	50	60	Ω
R _{IN,} D _{IFF}	Differential Input Resistance	IN to nIN, V _T = open		80	100	120	C

NOTE 1: Common mode input voltage is defined as V_{IH}.

To:

Table 4B. LVCMOS/LVTTL Input DC Characteristics, V_{DD} = V_{DDO} = 2.5V, T_A = -40°C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage			1.7		V _{DD} + 0.3	V
V _{IL}	Input Low Voltage			-0.3		0.7	V
I _{IH}	Input High Current	FSEL1, FSEL0, ADR[1:0]	$V_{DD} = V_{IN} = 2.625V$			150	μΑ
		SCK, SDA	$V_{DD} = V_{IN} = 2.625V$			5	μΑ
I _{IL}	Input Low Current	FSEL1, FSEL0, ADR[1:0]	V _{DD} = 2.625V, V _{IN} = 0V	-5			μΑ
		SCK, SDA	V _{DD} = 2.625V, V _{IN} = 0V	-150			μA
V _{IN}	Input Voltage Swing	IN, nIN		0.15		1.2	V
V _{CMR}	Common Mode Input Voltage; NOTE 1			1.2		V _{DD}	V
V _{DIFF}	Differential Input Voltage Swing	IN, nIN		0.3		2.4	v
R _{IN}	Input Resistance	IN, nIN to V _T		45	50	66	Ω
R _{IN,} D _{IFF}	Differential Input Resistance	IN to nIN, V _T = open		90	100	132	Ω

NOTE 1: Common mode input voltage is defined as V_{IH}.